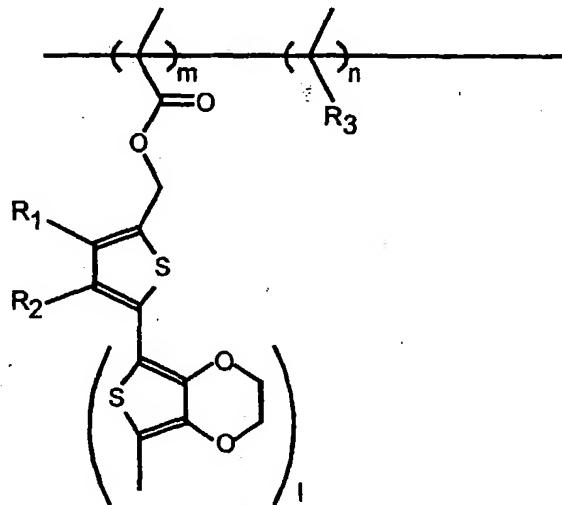


Abstract of the Disclosure:

A polymerizable composition for use in electron beam lithography, according to the following structural formula:



5 The formula use the following definitions. m is a number from 0.1 to 0.9. n is a number from 0.1 to 0.9 with $m+n=1$. I is an integer from 1 to 100. R_1 is H, an alkyl, a halogen, an amine, a silicon compound, or a germanium compound, having a chain length of up to six carbon, silicon, or germanium atoms.

10 R_2 is H, an alkyl, a halogen, an amine, a silicon group, or a germanium compound, having a chain length of up to six carbon, silicon, or germanium atoms. R_3 is an organic protective group which can be eliminated. A resist and a process using the resist utilize the polymerizable composition. The use of the

15 polymerizable composition in a resist reduces or prevents charging of a substrate at high exposure sensitivity.